

Stanford



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LINKS

- Google Scholar: <https://scholar.google.com/citations?hl=en&user=IvjzwxYAAAAJ>

Publications

PUBLICATIONS

- **Design Guidelines for Oxide Semiconductor Gain Cell Memory on a Logic Platform** *IEEE TRANSACTIONS ON ELECTRON DEVICES*
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- **High-speed and large-scale intrinsically stretchable integrated circuits.** *Nature*
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Liu, S., Li, S., Lin, Q., Jana, K., Mitra, S., Wong, H., Toprasertpong, K.
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